



TSCD114D

NPN Digital Transistor

SOT-363



Pin assignment:

1. TR1 Gnd (Emitter)
2. TR1 Input (Base)
3. TR2 Output (Collector)
4. TR2 Gnd (Emitter)
5. TR2 Input (Base)
6. TR1 Output (Collector)

$V_{CC} = 50V$
 $V_{in} = -6V \sim +40V$
 $I_o = 70mA(max.)$

Features

- ✧ Build-in bias resistor enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
- ✧ The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. The also have the advantage of almost completely eliminating parasitic effects.
- ✧ Only the on/off conditions need to be set for operation, making device design easy.
- ✧ Two TSC114D chips in a SOT-363 package
- ✧ Transistor elements are independent, eliminating interference
- ✧ Complements the TSAD114D

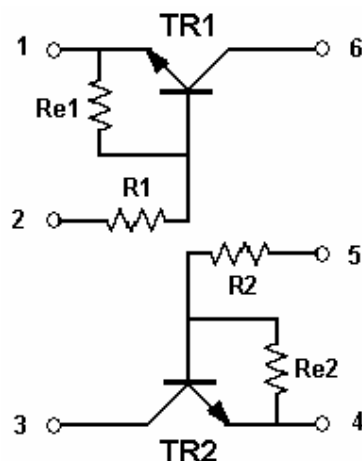
Ordering Information

Part No.	Packing	Package
TSCD114DCU6	Tape & Reel	SOT-363

Note: the build-in resistor value type, option as

No.	Re (K Ω)	R (K Ω)	Marking
TR 1	10	47	7D
TR 2	10	47	

Equivalent Circuit



$R1=4.7k\Omega$, $R2=4.7k\Omega$
 $Re1=47k\Omega$, $Re2=47k\Omega$

Absolute Maximum Rating ($T_a = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{in}	- 6 ~ +40	V
Output Current		DC	mA
		Pulse	
Power Dissipation (note)	P_D	200	mW
Operating Junction Temperature	T_J	+150	$^\circ C$
Operating Junction and Storage Temperature Range	T_{STG}	- 55 to +150	$^\circ C$

Note: 1. Single pulse, $P_w = 300\mu S$, Duty $\leq 2\%$
2. 150mW per element must not be exceeded.



Electrical Characteristics

Ta = 25 °C unless otherwise noted

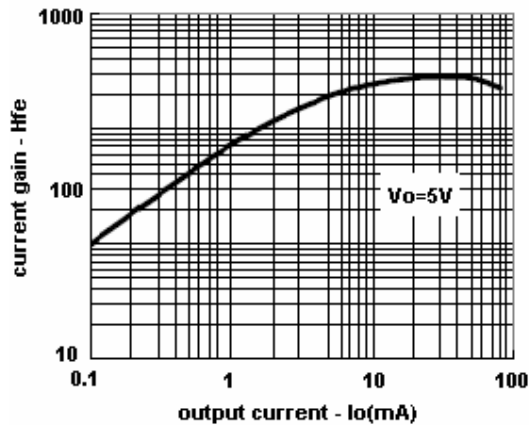
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Input Voltage	Vcc= 5V, Io= 100uA	Vin(off)	--	--	0.3	V
	Vo= 0.3V, Io= 1mA	Vin(on)	3	--	--	V
Output Voltage	Io/Iin= 5mA/ 0.25mA	Vo(on)	--	0.1	0.3	V
Input Current	Vin= 5V	Iin	--	--	0.88	mA
Output Current	Vcc= 50V, Vin= 0V	Io(off)	--	--	0.5	uA
DC Current Gain	Vo= 5V, Io= 5mA	Gi	68	--	--	
Input Resistance		R1	0.7	10	1.3	KΩ
Resistance Ratio		R2/R1	0.8	4.7	1.2	
Transition Frequency	Vce= 10V, Ie= 5mA, f= 100MHz (note 1)	ft	--	250	--	MHz

Note : 1. Transition frequency of the device.

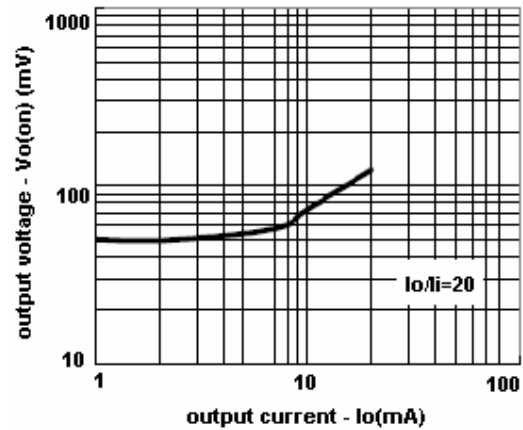
2. Pulse test: pulse width ≤380uS, duty cycle ≤2%

Electrical Characteristics Curve

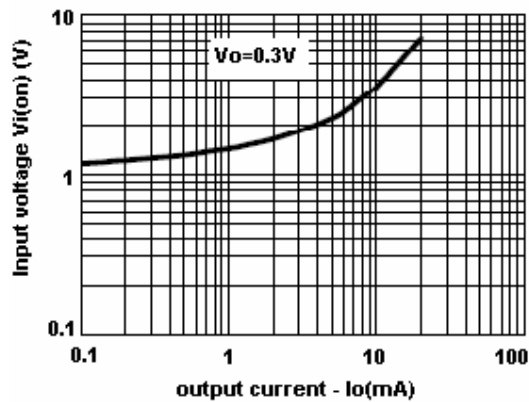
current gain vs output current



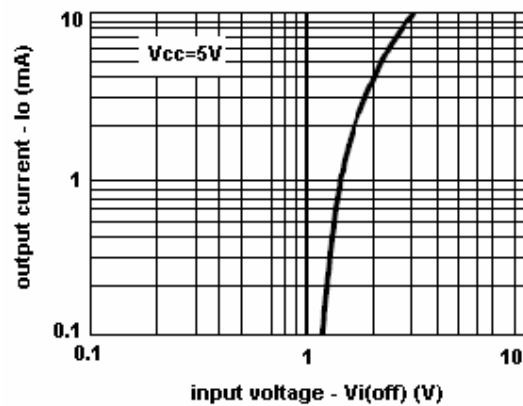
output voltage vs output current



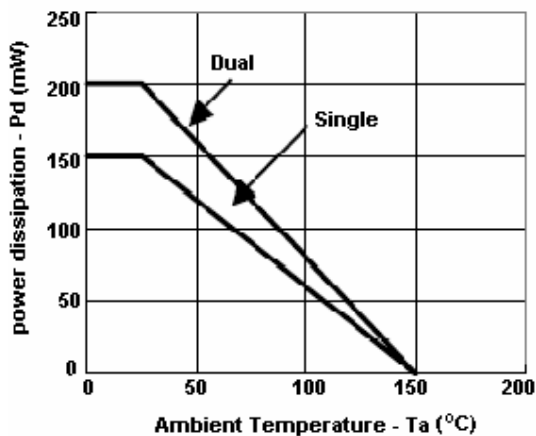
input voltage vs output current (on)



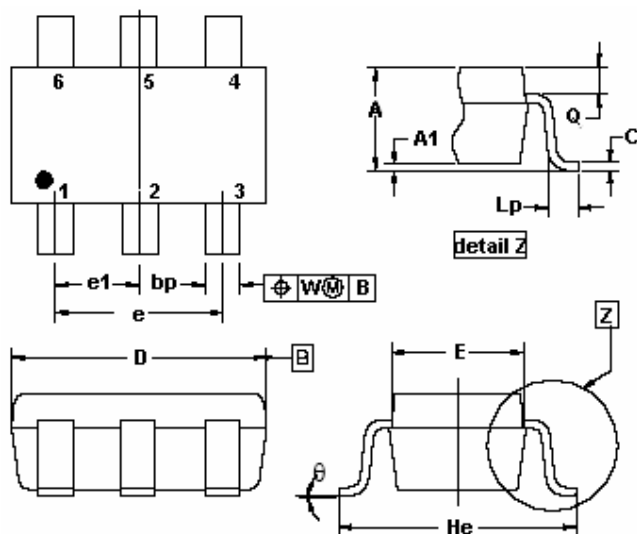
output current vs input voltage (off)



power dissipation vs temperature



SOT-363 Mechanical Drawing



SOT-363 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	1.10	0.031	0.043
A1	--	0.10	--	0.004
bp	0.10	0.30	0.004	0.012
C	0.10	0.25	0.004	0.010
D	1.80	2.20	0.071	0.087
E	1.15	1.35	0.045	0.053
e	1.30 (typ)		0.052 (typ)	
e1	0.65 (typ)		0.026 (typ)	
He	2.00	2.20	0.079	0.087
Lp	0.10	0.3	0.004	0.012
Q	0.20 (typ)		0.008 (typ)	
W	0.20 (typ)		0.008 (typ)	
Θ	10° (typ)		10° (typ)	